

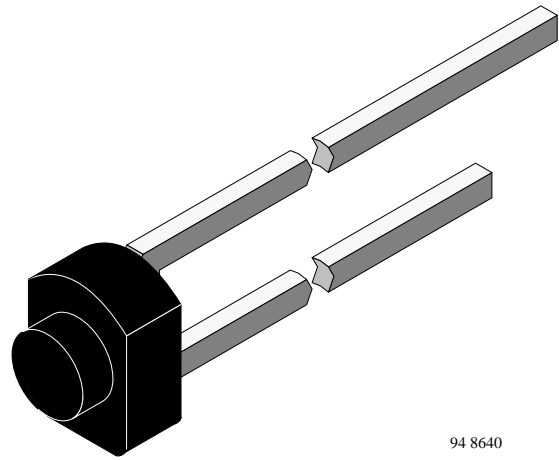
# Silicon NPN Phototransistor

## Description

S350P is a high sensitive silicon NPN epitaxial planar phototransistor in a miniature plastic case with flat window.

With a lead center-to-center spacing of 2.54mm and a package width of 2.4mm the devices are easily stackable on PC boards and assembled to arrays of unlimited size.

The epoxy package itself is an IR filter, spectrally matched to GaAs IR emitters with  $\lambda_p > 850\text{nm}$ .



94 8640

## Features

- High radiant sensitivity
- Miniature T- $\frac{3}{4}$  flat plastic package with IR filter
- Very wide angle of half sensitivity  $\phi = \pm 40^\circ$
- Suitable for near infrared radiation
- Suitable for 0.1" (2.54 mm) center-to-center spacing

## Applications

Detector in electronic control and drive circuits

## Absolute Maximum Ratings

$T_{\text{amb}} = 25^\circ\text{C}$

Parameter	Test Conditions	Symbol	Value	Unit
Collector Emitter Voltage		$V_{\text{CEO}}$	32	V
Emitter Collector Voltage		$V_{\text{ECO}}$	5	V
Collector Current		$I_{\text{C}}$	50	mA
Peak Collector Current	$t_p/T = 0.5, t_p \leq 10 \text{ ms}$	$I_{\text{CM}}$	100	mA
Total Power Dissipation	$T_{\text{amb}} \leq 55^\circ\text{C}$	$P_{\text{tot}}$	100	mW
Junction Temperature		$T_{\text{j}}$	100	$^\circ\text{C}$
Storage Temperature Range		$T_{\text{stg}}$	-55...+100	$^\circ\text{C}$
Soldering Temperature	$t \leq 3 \text{ s}$	$T_{\text{sd}}$	260	$^\circ\text{C}$
Thermal Resistance Junction/Ambient		$R_{\text{thJA}}$	450	K/W

### Basic Characteristics

$T_{amb} = 25^{\circ}\text{C}$

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
Collector Emitter Breakdown Voltage	$I_C = 1\text{ mA}$	$V_{(BR)CE}$ $V_O$	32			V
Collector Dark Current	$V_{CE} = 20\text{ V}, E = 0$	$I_{CEO}$		2	200	nA
Collector Emitter Capacitance	$V_{CE} = 5\text{ V}, f = 1\text{ MHz}, E=0$	$C_{CEO}$		6		pF
Collector Light Current	$E_e = 1\text{ mW/cm}^2,$ $\lambda = 950\text{ nm}, V_{CE} = 5\text{ V}$	$I_{ca}$	0.2	1		mA
Angle of Half Sensitivity		$\phi$		$\pm 40$		deg
Wavelength of Peak Sensitivity		$\lambda_p$		925		nm
Range of Spectral Bandwidth		$\lambda_{0.5}$		860...990		nm
Collector Emitter Saturation Voltage	$E_e = 1\text{ mW/cm}^2,$ $\lambda = 950\text{ nm}, I_C = 0.1\text{ mA}$	$V_{CEsat}$			0.3	V
Turn-On Time	$V_S = 5\text{ V}, I_C = 5\text{ mA},$ $R_L = 100\ \Omega$	$t_{on}$		6		$\mu\text{s}$
Turn-Off Time	$V_S = 5\text{ V}, I_C = 5\text{ mA},$ $R_L = 100\ \Omega$	$t_{off}$		5		$\mu\text{s}$
Cut-Off Frequency	$V_S = 5\text{ V}, I_C = 5\text{ mA},$ $R_L = 100\ \Omega$	$f_c$		110		kHz

### Typical Characteristics ( $T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified)

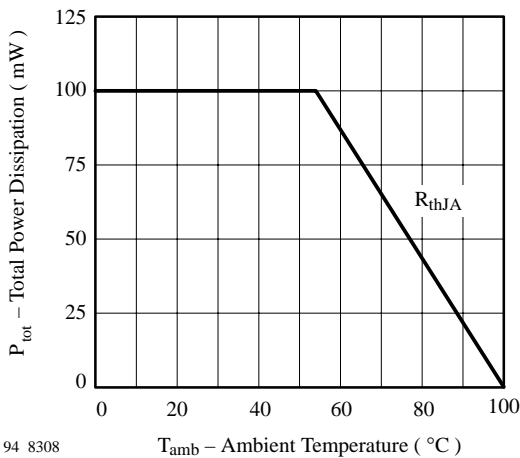


Figure 1. Total Power Dissipation vs. Ambient Temperature

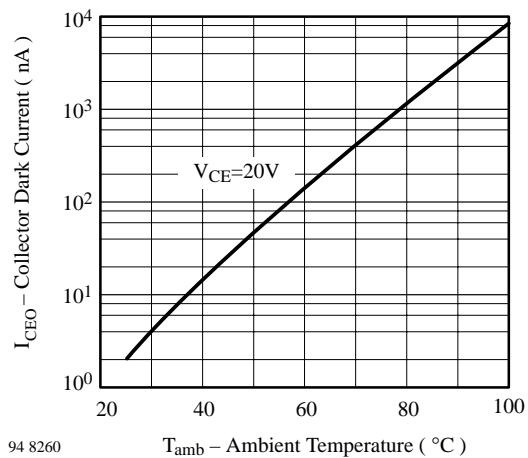
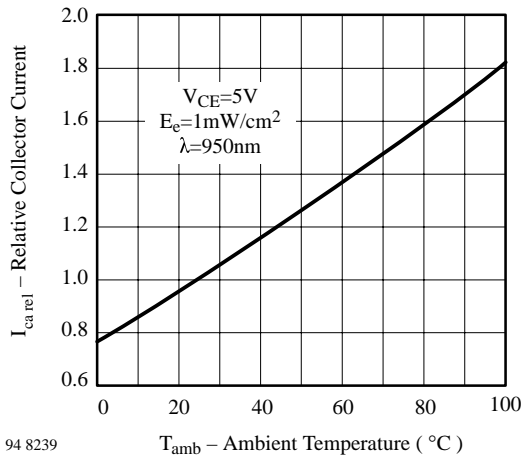
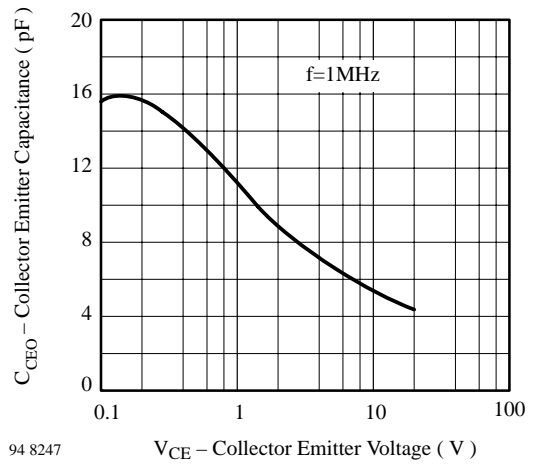


Figure 2. Collector Dark Current vs. Ambient Temperature



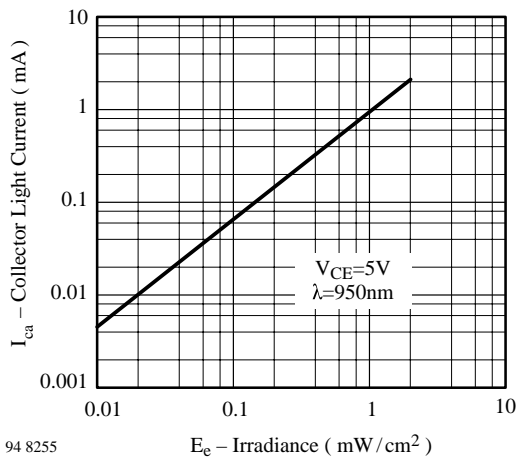
94 8239  $T_{amb}$  – Ambient Temperature ( °C )

Figure 3. Relative Collector Current vs. Ambient Temperature



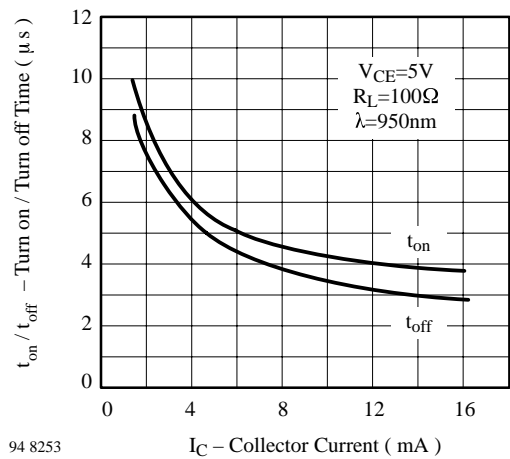
94 8247  $V_{CE}$  – Collector Emitter Voltage ( V )

Figure 6. Collector Emitter Capacitance vs. Collector Emitter Voltage



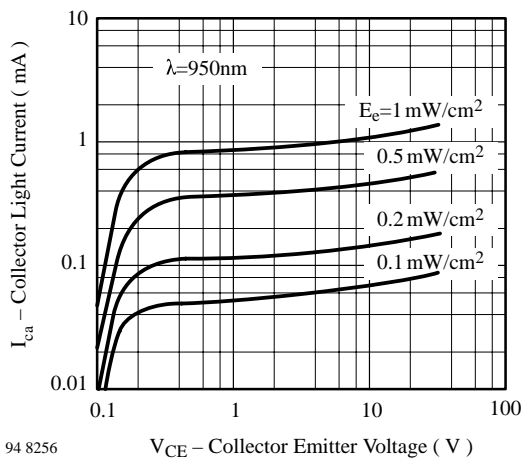
94 8255  $E_e$  – Irradiance ( mW/cm<sup>2</sup> )

Figure 4. Collector Light Current vs. Irradiance



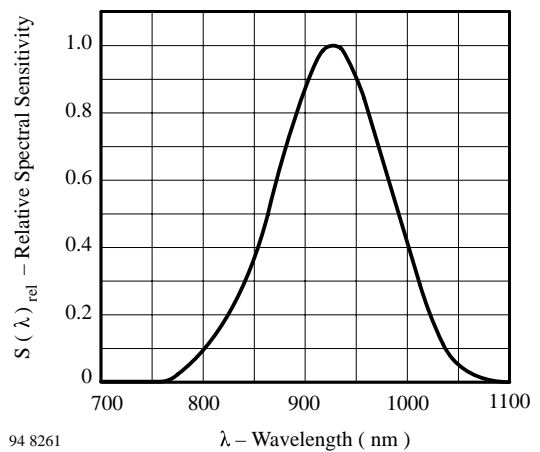
94 8253  $I_C$  – Collector Current ( mA )

Figure 7. Turn On/Turn Off Time vs. Collector Current



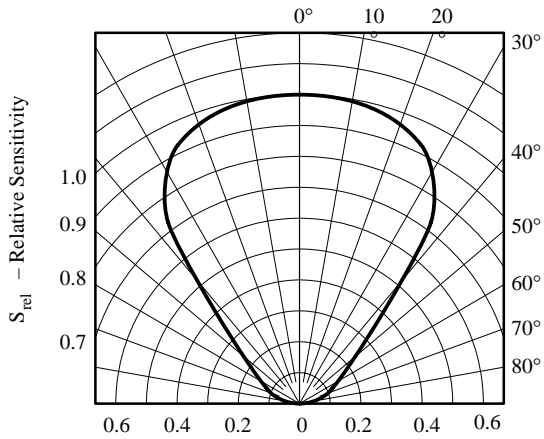
94 8256  $V_{CE}$  – Collector Emitter Voltage ( V )

Figure 5. Collector Light Current vs. Collector Emitter Voltage



94 8261  $\lambda$  – Wavelength ( nm )

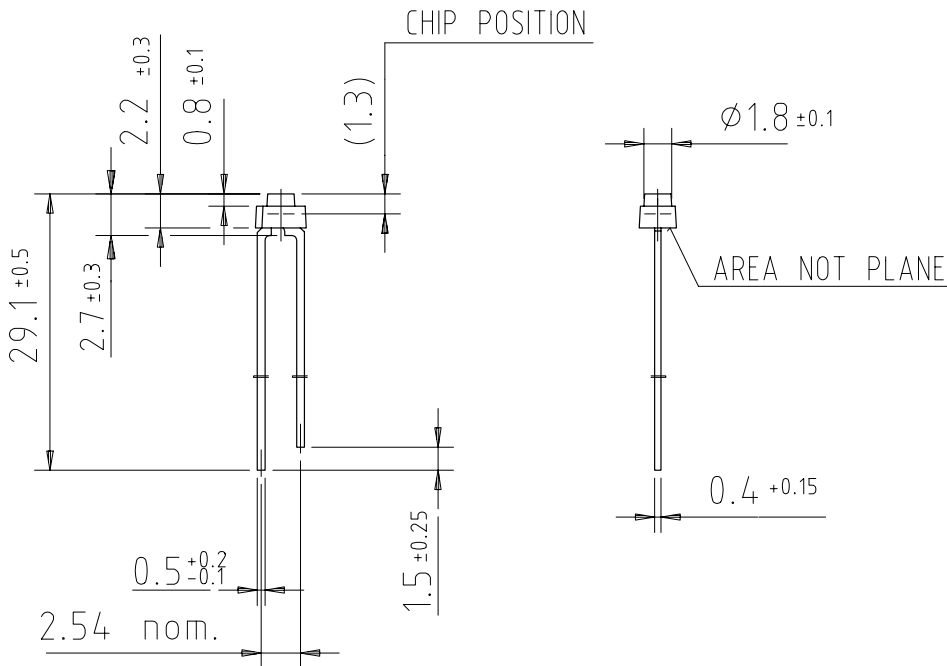
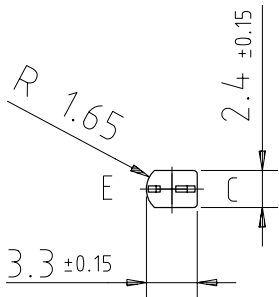
Figure 8. Relative Spectral Sensitivity vs. Wavelength



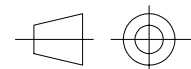
94 8257

Figure 9. Relative Radiant Sensitivity vs. Angular Displacement

Dimensions in mm



96 12188



technical drawings according to DIN specifications



## **Ozone Depleting Substances Policy Statement**

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

**Vishay Semiconductor GmbH** has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

**Vishay Semiconductor GmbH** can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

**We reserve the right to make changes to improve technical design and may do so without further notice.**

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay-Telefunken products for any unintended or unauthorized application, the buyer shall indemnify Vishay-Telefunken against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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